



### 150V N-Channel Enhancement Mode MOSFET

Voltage

150 V

Current

25 A

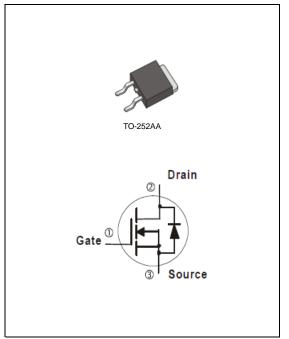
#### **Features**

- R<sub>DS(ON)</sub>, V<sub>GS</sub>@10V,I<sub>D</sub>@5A<65mΩ</li>
- $R_{DS(ON)}$ ,  $V_{GS}@6V$ ,  $I_{D}@3A<90m\Omega$
- High switching speed
- Improved dv/dt capability
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS2.0 (2011/65/EU & 2015/865/EU directive)
- Green molding compound as per IEC61249 Std. (Halogen Free)

### **Mechanical Data**

• Case: TO-252AA Package

• Terminals: Solderable per MIL-STD-750, Method 2026



# **Maximum Ratings and Thermal Characteristics** (T<sub>A</sub>=25 °C unless otherwise noted)

PARAMETE	ER	SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		$V_{DS}$	150	V	
Gate-Source Voltage		$V_{GS}$	<u>+</u> 25	V	
Continuous Dunin Comment	T <sub>C</sub> =25°C	I <sub>D</sub>	25		
Continuous Drain Current	T <sub>C</sub> =100°C		16	Α	
Pulsed Drain Current (Note 1)	T <sub>C</sub> =25°C	I <sub>DM</sub>	100		
Barran Birarin atian	T <sub>C</sub> =25°C	102	10/		
Power Dissipation	T <sub>C</sub> =100°C	Po	41	W	
0 11 0 1	T <sub>A</sub> =25°C	3.5	А		
Continuous Drain Current	T <sub>A</sub> =70°C	$I_D$	2.8	А	
Power Dissipation	T <sub>A</sub> =25°C	-	2.0	W	
Power Dissipation	T <sub>A</sub> =70°C	Pb	1.3		
Single Pulse Avalanche Energy (Note 6)		E <sub>AS</sub>	242	mJ	
Operating Junction and Storage Temperature Range		$T_J, T_{STG}$	-55~150	°C	
T (Note 4.5)	Junction to Case	$R_{ heta JC}$	1.23	°C/W	
Typical Thermal Resistance <sup>(Note 4,5)</sup>	Junction to Ambient	$R_{\theta JA}$	62.5		

• Limited only By Maximum Junction Temperature





### **Electrical Characteristics** (T<sub>A</sub>=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static			1	•	•	1
Drain-Source Breakdown Voltage	$BV_{DSS}$	V <sub>GS</sub> =0V,I <sub>D</sub> =250uA	150	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_{D}=250uA$	2.0	2.7	4.0	V
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	$V_{GS}=10V,I_{D}=5A$	-	50	65	mΩ
		$V_{GS}=6V,I_{D}=3A$	-	60	90	
Zero Gate Voltage Drain Current	$I_{DSS}$	V <sub>DS</sub> =150V,V <sub>GS</sub> =0V	-	-	1.0	uA
Gate-Source Leakage Current	$I_{GSS}$	V <sub>GS</sub> = <u>+</u> 25V,V <sub>DS</sub> =0V	-	-	<u>+</u> 100	nA
Dynamic (Note 7)						
Total Gate Charge	$Q_{g}$	$V_{DS}$ =75V, $I_{D}$ =4A, $V_{GS}$ =10V (Note 1,2)	-	29.5	-	nC
Gate-Source Charge	$Q_gs$		-	9.2	-	
Gate-Drain Charge	$Q_gd$		-	8.0	-	
Input Capacitance	Ciss	$V_{DS}$ =30V, $V_{GS}$ =0V, $f$ =1.0MHZ	-	1764	-	pF
Output Capacitance	Coss		-	148	-	
Reverse Transfer Capacitance	Crss		-	62	-	
Turn-On Delay Time	td <sub>(on)</sub>	$V_{DS}$ =30V, $I_{D}$ =1A, $V_{GS}$ =10V, $R_{G}$ =6 $\Omega$ (Note 1,2)	-	14	-	
Turn-On Rise Time	t <sub>r</sub>		-	21	-	ns
Turn-Off Delay Time	td <sub>(off)</sub>		-	32	-	
Turn-Off Fall Time	t <sub>f</sub>		-	23	-	
Drain-Source Diode						
Maximum Continuous Drain-Source	1		-	-	25	А
Diode Forward Current	Is					
Diode Forward Voltage	$V_{SD}$	I <sub>S</sub> =1A,V <sub>GS</sub> =0V	-	0.7	1.0	V

### NOTES:

- 1. Pulse width<a></a>300us, Duty cycle<a></a>2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature TJ(MAX)=150°C. Ratings are based on low frequency and duty cycles to keep initial TJ =25°C.
- 4. The maximum current rating is package limited.
- 5. R@JA is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch<sup>2</sup> with 2oz.square pad of copper.
- 6. The test condition is L=0.1mH,  $I_{AS}$ =22A,  $V_{DD}$ =50V,  $V_{GS}$ =10V
- 7. Guaranteed by design, not subject to production testing.





### **TYPICAL CHARACTERISTIC CURVES**

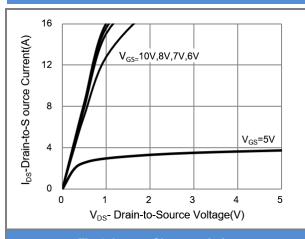


Fig.1 Output Characteristics

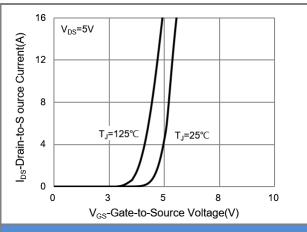


Fig.2 Transfer Characteristics

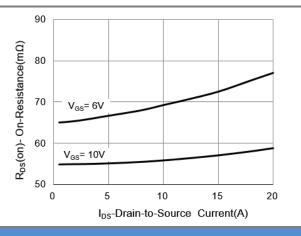


Fig.3 On-Resistance vs. Drain Current

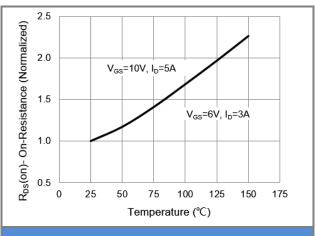


Fig.4 On-Resistance vs. Junction temperature

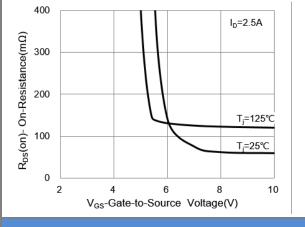


Fig.5 On-Resistance Variation with VGS.

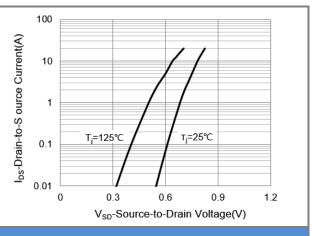


Fig.6 Source-Drain Diode Forward Voltage





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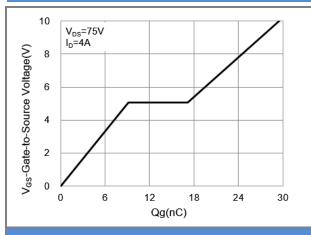


Fig.7 Gate-Charge Characteristics

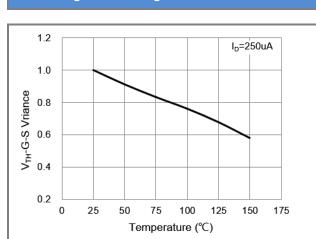
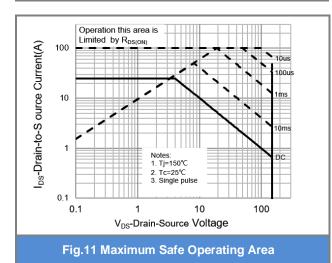


Fig.9 Threshold Voltage Variation with Temperature



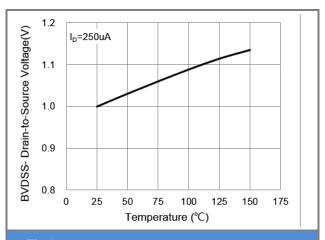


Fig.8 Breakdown Voltage Variation vs. Temperature

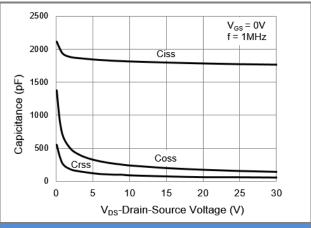


Fig.10 Capacitance vs. Drain-Source Voltage





### **TYPICAL CHARACTERISTIC CURVES**

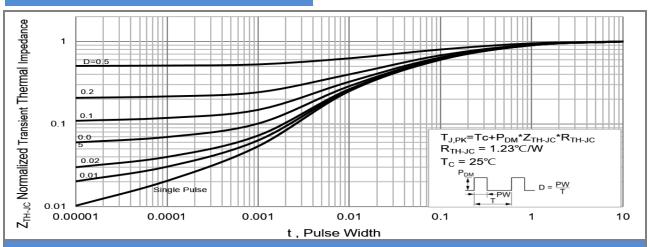
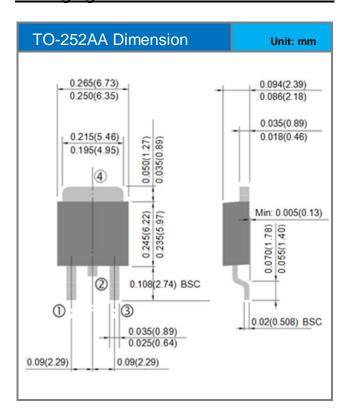


Fig.12 Normalized Transient Thermal Impedance vs. Pulse Width





### **Packaging Information**



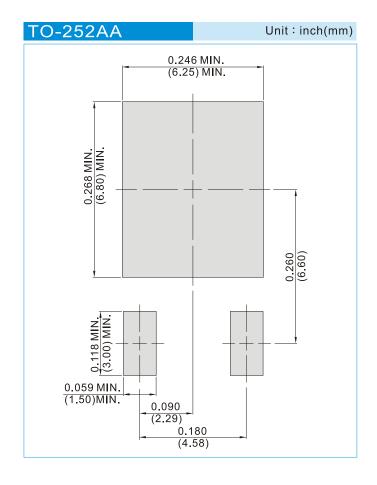




### PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing Type	Marking	Version	
PJD30N15_L2_00001	TO-252AA	3,000pcs / 13" reel	D30N15	Halogen free	

### **MOUNTING PAD LAYOUT**



November 25,2016-REV.00 Page 7





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